

ABSTRACT OF THE DISCLOSURE

A method for fabricating a semiconductor memory device includes the consecutive steps of consecutively depositing 5 metallic, nitride and oxide films on an underlying insulating film, patterning the nitride and oxide films to allow the oxide film to have a patterned area smaller than the patterned area of the nitride film, patterning the metallic film by using the nitride and oxide films as a mask, forming a side-wall film having a tapered mesa 10 structure on the oxide, nitride and metallic films, embedding the side-wall oxide film by an interlayer dielectric film, and forming a contact hole in the interlayer dielectric film and the underlying oxide film while using the side-wall oxide film as an etch stopper.